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Semiconductor devices – Micro-electromechanical devices – Part 8: Strip bending test method for tensile property measurement of thin films

Dispositifs à semiconducteurs – Dispositifs microélectromécaniques – Partie 8: Méthode d'essai de la flexion de bandes en vue de la mesure des propriétés de traction des couches minces 47-8-2011





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SEMICONDUCTOR DEVICES – MICRO-ELECTROMECHANICAL DEVICES –

Part 8: Strip bending test method for tensile property measurement of thin films

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The text of this standard is based on the following documents:

FDIS	Report on voting
47F/71/FDIS	47F/77/RVD

Full information on the voting for the approval of this standard can be found in the report on voting indicated in the above table.

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SEMICONDUCTOR DEVICES -MICRO-ELECTROMECHANICAL DEVICES -

Part 8: Strip bending test method for tensile property measurement of thin films

1 Scope

This international standard specifies the strip bending test method to measure tensile properties of thin films with high accuracy, repeatability, moderate effort of alignment and handling compared to the conventional tensile test. This testing method is valid for test pieces with a thickness between 50 nm and several μ m, and with an aspect ratio (ratio of length to thickness) of more than 300.

The hanging strip (or bridge) between two fixed supports are widely adopted in MEMS or micro-machines. It is much easier to fabricate these strips than the conventional tensile test pieces. The test procedures are so simple to be readily automated. This international standard can be utilized as a quality control test for MEMS production since its testing throughput is very high compared to the conventional tensile test.

iTeh STANDARD PREVIEW Normative references

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The following referenced documents are indispensable for the application of this document. For dated references, only the edition cited applies. For undated references, the latest edition of the referenced document (including any amendments) applies -48e2-bf5e-

NONE

2

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3 Terms and definitions

For the purposes of this document the following terms and definitions apply.

3.1

deflection

w

displacement of a test piece at the middle of the length, which is measured with respect to the straight line connecting two fixed ends of the test piece

3.2

deflection angle

β

angle between the deformed test piece and the straight line connecting two fixed ends of the test piece

NOTE Test piece in this document is often referred to as a strip bending specimen.

4 Test apparatus

4.1 General

A test apparatus is composed of an actuator, a load-sensor, a displacement sensor, and alignment mechanism as other mechanical testers such as micro-tensile tester and nanoindentation apparatus. A test piece in a form of strip is very compliant and experiences large deflection under a small load when comparing it with a micro-tensile test piece with similar dimensions. In this respect, the load-sensor should have an excellent resolution and the displacement sensor should have a long measuring range. Details on each component of test apparatus are described as follows.

4.2 Actuator

All actuating devices that are capable of linear movement can be used for the test, e.g. piezoelectric actuator, voice coil actuator, servo motor, etc. However, a device with fine displacement resolution is highly recommended due to small dimensions of the test piece. The resolution shall be better than 1/1 000 of maximum deflection of test piece.

4.3 Load tip

The load tip which applies a line contact force to the test piece is shaped like a conventional wedge type indenter tip and can be made of diamond, sapphire or other hard materials. The radius of the tip shall be comparable to or larger than the thickness of the test piece, and less than L/50 (refer to Annex C.3).

4.4 Alignment mechanism

The load tip shall be installed on the test apparatus aligned with the load and the displacement measuring axes, and the misalignment shall be less than 1 degree. The load tip shall be also aligned to the surface of the test piece with the deviation angles less than 1 degree (refer to Annex C for definition of deviation angles and error estimation of misalignment). It is desirable to equip the apparatus with tilt stages for adjusting the deviation angle. The load tip is to be positioned at the centre of the test piece and the positional accuracy shall be less than L/100.

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4.5 Force and displacementisen/sors/standards/sist/40cb803a-f6eb-48e2-bf5e-

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Force and displacement sensors shall have resolutions better than $1/1\ 000$ of the maximum force and deflection during the test. The accuracy of the sensors shall be within ± 1 % of the range. The displacement sensors can be capacitive type, LVDT type, or optical type with acceptable resolution and accuracy. In practice, the deflection can be measured from the motion of the load tip using a capacitive sensor or from the deflection of the test piece using an optical method.

4.6 Test environment

It is recommended to perform a test under constant temperature and humidity. Temperature change can induce thermal drift during deflection measurement. The temperature change or thermal drift shall be checked before and after the test.

5 Test piece

5.1 General

The test piece shall be prepared by using the same fabrication process as the actual device fabrication. To minimize the size effect of a test piece, the structure and size of the test piece shall be similar to those of the device components.

There are many fabrication methods of the test piece depending on the applications. As an example, the fabrication of the test piece based on MEMS process is described in Annex B. A lot of strip bending test pieces can be fabricated on a die or a substrate.

5.2 Shape of test piece

The shape of test piece and symbols are given in Figure 1 and Table 1, respectively. The test piece shall be designed to minimize the bending moment effect. In order to minimize the effect, the maximum deflection shall be more than 40 times the thickness of the test piece, and the length of the test piece shall be more than 300 times the thickness of the test piece, and the width shall be more than 10 times the thickness of the test piece, and the length shall be 10 times larger than the width. The thickness of the substrate shall be more than 500 times that of the test piece. The dimension of the substrate is limited by the capacity of the test apparatus. The geometry of the fixed ends supporting the test piece can affect the test results. When etching the sacrificial layer and the supporting substrate of test pieces, the region beneath the test pieces can be over-etched, and this is called by under-cut. The under-cut at the fixed ends shall be minimized (anisotropic etching would be desirable rather than isotropic etching).



Figure 10-10 him film test piece

Symbol	Unit	Designation
l_1	μm	Length of a test piece (=2L)
l_2	μm	Width of a test piece (= <i>B</i>)
l ₃	μm	Thickness of a test piece (= <i>h</i>)

5.3 Measurement of test piece dimension

To analyze the test results, the accurate measurement of the test piece dimensions is required since the dimensions are used to extract mechanical properties of test materials. The length (2*L*), width (*B*), and thickness (*h*) shall be measured with very high accuracy with less than \pm 5 % error. Useful information on thickness measurement can be found in Annex C of [1] ¹ and in Clause 6 of [2].

¹ Figures in square brackets refer to the Bibliography.

6 Test procedure and analysis

6.1 General

- a) The substrate containing test pieces is attached to a sample holder. There are some recommendable methods for the sample attachment, such as magnetic attachment, electrostatic gripping, adhesive gluing, etc.
- b) The translational and angular misalignment between the load tip and the test piece can affect the test results (refer to Figure C.2), and should be checked using an optical microscope. The misalignment error and the guideline for alignment are described in Annex C.
- c) It is necessary to determine surface location of a test piece at the beginning of the test. The surface location is the position of the top surface of the test piece in the vertical direction when the strip deforms by the vertical movement of the load tip. This surface location can be determined by optical inspection using an optical microscope, or be determined by three successive indents. When the load tip touches the strip, the slight change in the strip configuration can be observed and identified using the optical microscope. The detailed method for determining the surface location using three successive indents is described in A.3.
- d) The test is performed under a constant displacement rate until the strip ruptures. The displacement rate of $L \times 10^{-4}/s$ or $L \times 10^{-3}/s$ is recommended, which leads to the strain rate of approximately $1 \times 10^{-5}/s$ or $1 \times 10^{-4}/s$, respectively when the strain reaches 0,5 %. This method applies to strain rate insensitive materials since the strain rate changes during the test. **The STANDARD PREVIEW**

6.2 Data analysis

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To obtain an actual force and deflection data of a test piece from the experimental results, several compensations may be required depending on the test apparatus. As an example, the data analysis procedures can provide useful information for other types of apparatus. These procedures can provide useful information for other types of apparatus. From the force and deflection measurements, stress and strain can be estimated by the following Equations (1) and (2). The equations are derived on the assumptions of negligible bending moment effect and uniform strain throughout the test piece [1-3]. See Figure 2.

$$\sigma = \frac{F}{2Bh\sin\beta},\tag{1}$$

$$\varepsilon = \frac{\sqrt{L^2 + w^2}}{L} - l.$$
 (2)

Here, σ is the strip stress, \mathcal{E} is the strip strain, F is the force applied to a test piece during test and w is its corresponding deflection, β is defined as $\tan^{-1}(w/L)$. When L/h is larger than 300, these equations yield an excellent estimation of elastic modulus and yield strength as verified in Annex C. The effect of internal stress or residual stress could be considered with this method. When the internal stress exists, "F" in the equation (1) is affected by the internal stress and the strip stress changes also. The buckled test piece is excluded in this standard.



Figure 2 – Schematic of strip bending test

Test report 7

The test report shall contain at least the following information;

- a) reference to this international standard;
- b) identification number of the test piece DARD PREVIEW
- c) fabrication procedures of the test piece ards.iteh.ai)
- d) test piece material;
 - in case of single crystal: crystallographic/orientation
 - in case of poly crystal resture and grand sizes /40cb803a-f6eb-48e2-bf5e-f6a440c5fdd7/iec-62047-8-2011
- e) test piece dimension and measurement method;
- f) description of testing apparatus;
- g) measured properties and results: elastic modulus, tensile strength, yield strength and stress-strain curve.

Annex A (informative)

Data analysis: Test results by using nanoindentation apparatus

A.1 Cause of errors

Thermal drift, difficulty of finding the surface location of the test piece and leaf spring stiffness of test apparatus can affect the test results.

A.2 Thermal drift compensation

Thermal drift is a common cause of error for a precise sensor measurement. This error is regarded as the result of thermal fluctuation from the test system. To measure thermal drift, the deflection is recorded for a period of time under a load controlled condition while a test piece is in contact with the wedge tip. Using the drift data, the deflection data of the strip bending test are corrected. This is a common compensation method of a nanoindentation test. Since the creep deformation is not clearly distinguished from the thermal drift, this compensation is not used in case of a test piece with creep behaviour.

A.3 Determination of surface location RD PREVIEW

Finding the surface location of a test piece is very difficult is note the stiffness change is too small to detect when the wedge tip is in contact with the test piece. As an alternative method, the surface locations of the two fixed strip ends to substrate are measured and the average value of the surface locations is taken as the surface location of the strip. See Figure A.1. This method can determine a reference surface location for a wrinkled film caused by compressive residual stress. The deflection of a test piece is measured from that reference surface location.



Figure A.1 – Three successive indents for determining the reference location of a test piece



IEC 502/11

Figure A.2 – A schematic view of nanoindentation apparatus



NOTE The test piece is Au film with a thickness of 0,1 μ m, a width of 10 μ m, and a length of 400 μ m.

Figure A.3 – Actuator force vs. deflection curves for strip bending test and for leaf spring test

A.4 Leaf spring stiffness compensation

Many commercial nanoindenation systems are utilizing a leaf spring to achieve a highly repeatable linear motion. See Figure A.2. This apparatus applies a force on a test piece by controlling the electric current supplied to the electromagnetic actuator. The actuator force is obtained from the electric current multiplied by load calibration constant. The actual force on a test piece can be determined by subtraction of the force for the leaf spring deformation from the actuator force. The leaf spring force can be measured by moving actuator without any test piece. This is represented by the open circle curve in Figure A.3. In order to compensate for the leaf spring force, the force-deflection data without a test piece are subtracted from the force-deflection data with a test piece (the filled square curve in Figure A.3). The actual force